

OM SENI

NSR05F20NXT5G Schottky Barrier Diode

These Schottky barrier diodes are optimized for low forward voltage drop and low leakage current and are offered in a Chip Scale Package (CSP) to reduce board space. The low thermal resistance enables designers to meet the challenging task of achieving higher efficiency and meeting reduced space requirements.

Features

- Low Forward Voltage Drop – 390 mV @ 500 mA
- Low Reverse Current – 15 μ A @ 10 V VR
- 500 mA of Continuous Forward Current
- ESD Rating – Human Body Model: Class 3B
– Machine Model: Class C
- High Switching Speed
- These Devices are Pb-Free, Halogen Free/BFR Free and are RoHS Compliant

Typical Applications

- LCD and Keypad Backlighting
- Camera Photo Flash
- Buck and Boost dc–dc Converters
- Reverse Voltage and Current Protection
- Clamping & Protection

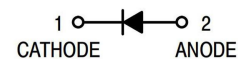
Markets

- Mobile Handsets
- MP3 Players
- Digital Camera and Camcorders
- Notebook PCs & PDAs
- GPS

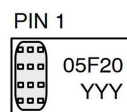
MAXIMUM RATINGS

Rating	Symbol	Value	Unit	
Reverse Voltage	V_R	20	V	
Forward Current (DC)	I_F	500	mA	
Forward Surge Current (60 Hz @ 1 cycle)	I_{FSM}	10	A	
Repetitive Peak Forward Current (Pulse Wave = 1 sec, Duty Cycle = 66%)	I_{FRM}	4.0	A	
ESD Rating:	Human Body Model Machine Model	ESD	> 8 > 400	kV V

20 V SCHOTTKY BARRIER DIODE



MARKING DIAGRAM



05F20 = Specific Device Code
YYY = Year Code

ORDERING INFORMATION

Device	Package	Shipping†
NSR05F20NXT5G	DSN2 (Pb-Free)	5000 / Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

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THERMAL CHARACTERISTICS

Characteristic	Symbol	Min	Typ	Max	Unit
Thermal Resistance Junction-to-Ambient (Note 1) Total Power Dissipation @ $T_A = 25^\circ\text{C}$	$R_{\theta JA}$ P_D			240 521	$^\circ\text{C/W}$ mW
Thermal Resistance Junction-to-Ambient (Note 2) Total Power Dissipation @ $T_A = 25^\circ\text{C}$	$R_{\theta JA}$ P_D			94 1.3	$^\circ\text{C/W}$ W
Storage Temperature Range	T_{stg}			-40 to +125	$^\circ\text{C}$
Junction Temperature	T_J			+150	$^\circ\text{C}$

1. Mounted onto a 4 in square FR-4 board 50 mm sq. 1 oz. Cu 0.06" thick single sided. Operating to steady state.
2. Mounted onto a 4 in square FR-4 board 1 in sq. 1 oz. Cu 0.06" thick single sided. Operating to steady state.

ELECTRICAL CHARACTERISTICS ($T_A = 25^\circ\text{C}$ unless otherwise noted)

Characteristic	Symbol	Min	Typ	Max	Unit
Reverse Leakage ($V_R = 10\text{ V}$) ($V_R = 20\text{ V}$)	I_R			15 75	μA
Forward Voltage ($I_F = 100\text{ mA}$) ($I_F = 500\text{ mA}$)	V_F		0.330 0.390	0.345 0.430	V

TYPICAL CHARACTERISTICS

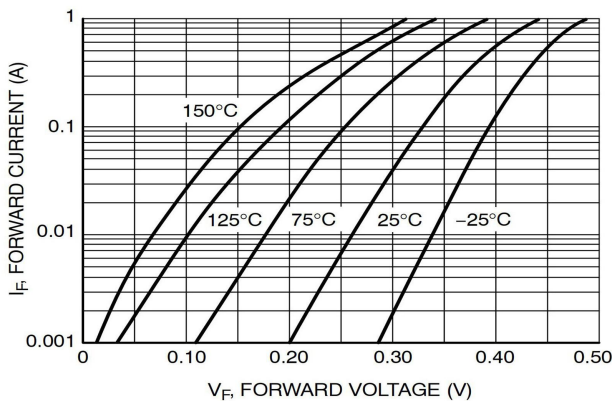


Figure 1. Forward Voltage

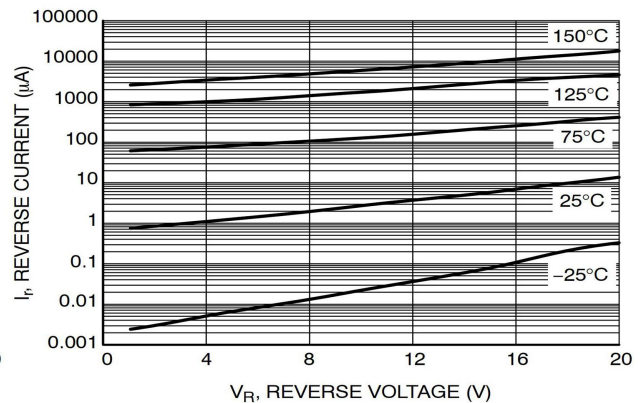


Figure 2. Leakage Current

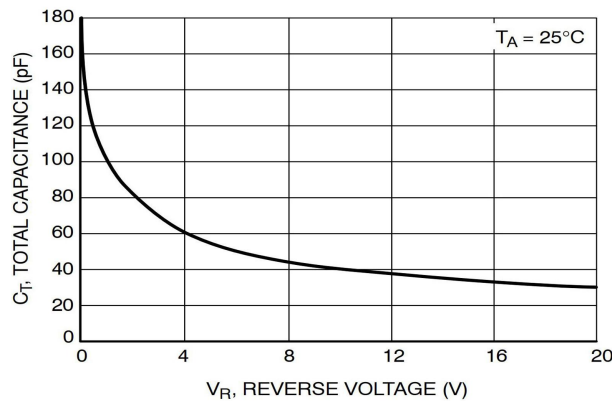
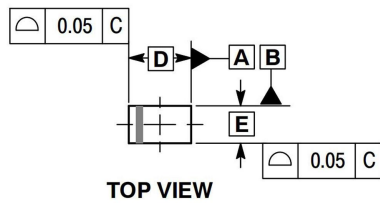


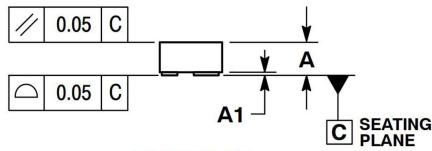
Figure 3. Total Capacitance

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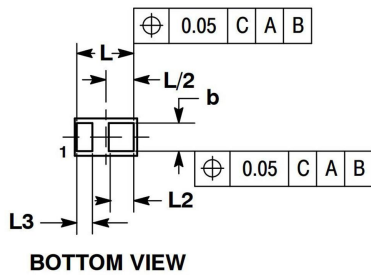
DSN2, 1.0x0.6, 0.575P, (0402)
 CASE 152AC-01
 ISSUE B



TOP VIEW



SIDE VIEW

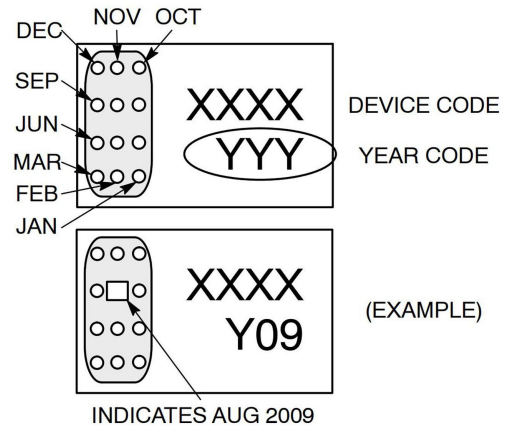


BOTTOM VIEW

- NOTES:
 1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
 2. CONTROLLING DIMENSION: MILLIMETERS.

MILLIMETERS		
DIM	MIN	MAX
A	0.25	0.31
A1	---	0.05
b	0.45	0.55
D	1.00 BSC	
E	0.60 BSC	
L	0.85	0.95
L2	0.35	0.45
L3	0.20	0.30

CATHODE BAND MONTH CODING



RECOMMENDED SOLDER FOOTPRINT*

